

IN THE CLAIMS:

1. (Currently Amended): A ferroelectric capacitor manufacturing method comprising the steps of:

- (a) forming a lower electrode on a base substrate having an insulating surface;
- (b) forming an oxide ferroelectric layer on said lower electrode; and
- (c) laminating a first and a second oxide upper electrodes onto said oxide ferroelectric layer by sputtering wherein one of said first and second oxide upper electrodes is sputtered using a target that comprises SRO ceramic that has an increased density by adding at least $[[0.1\text{at\%}]]$ 0.1 at % additive and the other of said first and second oxide upper electrodes is sputtered using a target comprising Ir.

2. (original): The ferroelectric capacitor manufacturing method as set forth in Claim 1, wherein said step (b) deposits an oxide ferroelectric layer by chemical vapor deposition or chemical solution deposition.

3. (original): The ferroelectric capacitor manufacturing method as set forth in Claim 1, wherein said step (b) deposits an oxide ferroelectric layer by at least one method among the group consisting of sputtering, chemical vapor deposition, and chemical solution deposition.

4. (original): The ferroelectric capacitor manufacturing method as set forth in Claim 1, wherein said step (c) comprises heating the base substrate.

5. (original): The ferroelectric capacitor manufacturing method as set forth in Claim 4, wherein said heating heats the base substrate to a temperature of at most 800°C.

6. (original): The ferroelectric capacitor manufacturing method as set forth in Claim 1, wherein said step (c) includes annealing at a temperature from 500°C to 800°C after sputtering of said one of the oxide upper electrodes.

7. (original): The ferroelectric capacitor manufacturing method as set forth in Claim 1, wherein said base substrate is a semiconductor substrate on which semiconductor elements are formed.